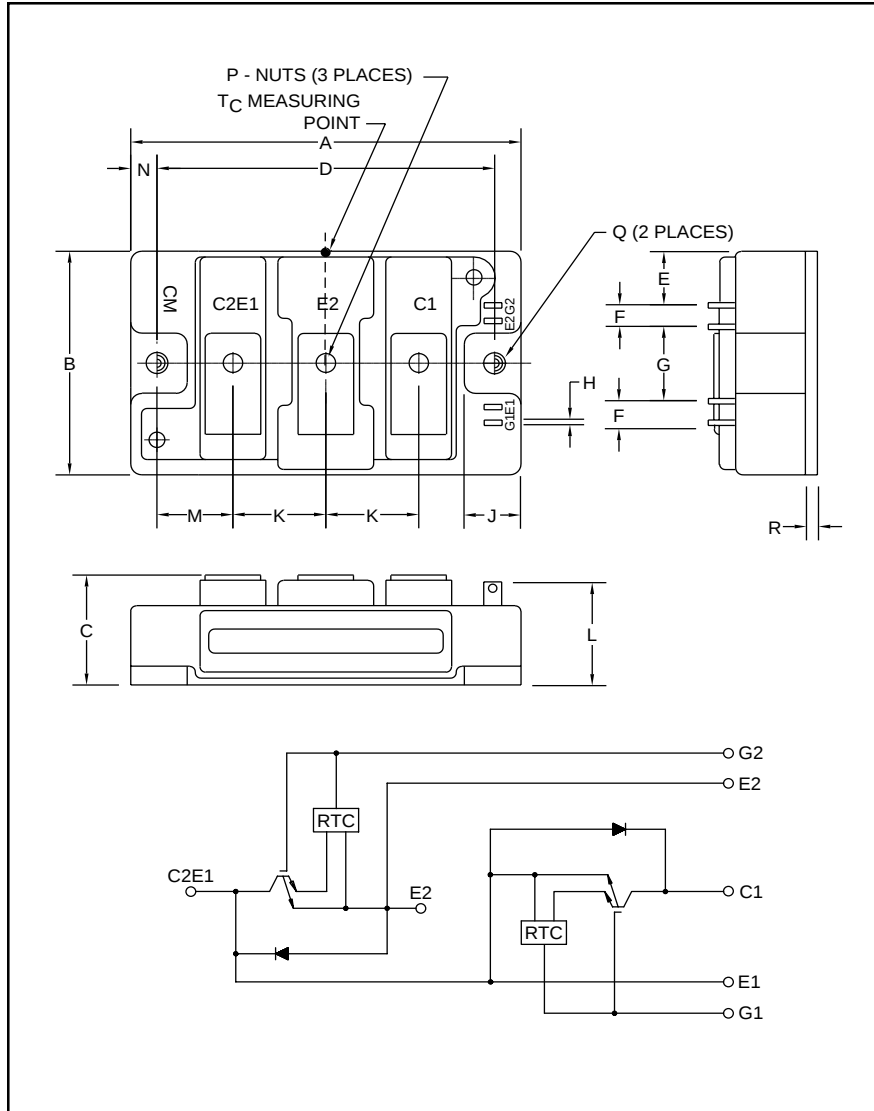


Trench Gate Design Dual IGBTMOD™ 100 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	3.70	94.0
B	1.89	48.0
C	1.18 +0.04/-0.02	30.0 +1.0/-0.5
D	3.15±0.01	80.0±0.25
E	0.43	11.0
F	0.16	4.0
G	0.71	18.0
H	0.02	0.5

Dimensions	Inches	Millimeters
J	0.53	13.5
K	0.91	23.0
L	1.13	28.7
M	0.67	17.0
N	0.28	7.0
P	M5	M5
Q	0.26 Dia.	6.5 Dia.
R	0.16	4.0



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ UPS
- ☐ Battery Powered Supplies

Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM100DU-24F is a 1200V (V_{CES}), 100 Ampere Dual IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	100	24

CM100DU-24F

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100 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	CM100DU-24F	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_c = 25^\circ\text{C}$)	I_C	100	Amperes
Peak Collector Current	I_{CM}	200*	Amperes
Emitter Current** ($T_c = 25^\circ\text{C}$)	I_E	100	Amperes
Peak Emitter Current**	I_{EM}	200*	Amperes
Maximum Collector Dissipation ($T_c = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)	P_c	500	Watts
Mounting Torque, M5 Main Terminal	–	31	in-lb
Mounting Torque, M6 Mounting	–	40	in-lb
Weight	–	310	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	Volts

Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0\text{V}$	–	–	1	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}$, $V_{CE} = 0\text{V}$	–	–	20	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 10\text{mA}$, $V_{CE} = 10\text{V}$	5	6	7	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100\text{A}$, $V_{GE} = 15\text{V}$, $T_j = 25^\circ\text{C}$	–	1.8	2.4	Volts
		$I_C = 100\text{A}$, $V_{GE} = 15\text{V}$, $T_j = 125^\circ\text{C}$	–	1.9	–	Volts
Total Gate Charge	Q_G	$V_{CC} = 600\text{V}$, $I_C = 100\text{A}$, $V_{GE} = 15\text{V}$	–	1100	–	nC
Emitter-Collector Voltage**	V_{EC}	$I_E = 100\text{A}$, $V_{GE} = 0\text{V}$	–	–	3.2	Volts

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

** Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

CM100DU-24F
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Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0V	–	–	39	nf
Output Capacitance		C _{oes}		–	–	1.7	nf
Reverse Transfer Capacitance		C _{res}		–	–	1	nf
Inductive	Turn-on Delay Time	t _{d(on)}	V _{CC} = 600V, I _C = 100A,	–	–	100	ns
Load	Rise Time	t _r	V _{GE1} = V _{GE2} = 15V,	–	–	50	ns
Switch	Turn-off Delay Time	t _{d(off)}	R _G = 3.1Ω,	–	–	400	ns
Times	Fall Time	t _f	Inductive Load	–	–	300	ns
Diode Reverse Recovery Time**		t _{rr}	Switching Operation	–	–	150	ns
Diode Reverse Recovery Charge**		Q _{rr}	I _E = 100A	–	4.1	–	μC

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/2 Module, T_C Reference Point per Outline Drawing	–		0.25	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/2 Module, T_C Reference Point per Outline Drawing	–	–	0.35	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)'Q}$	Per IGBT 1/2 Module, T_C Reference Point Under Chip	–	0.15		$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	–	0.035	–	$^\circ\text{C/W}$

** Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

CM100DU-24F

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